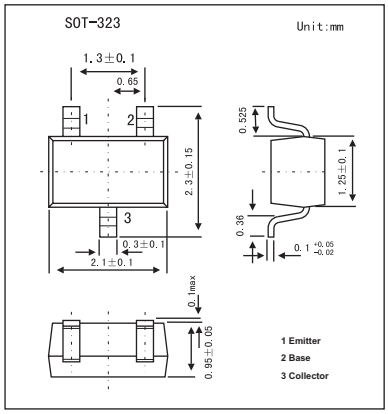
Silicon NPN Epitaxial Planar

2SC3936



■ Features

- Optimum for RF amplification, oscillation, mixing, and IF of FM/AM radios.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	30	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = 10μA, I_E = 0	30			V
Collector-emitter voltage	V_{CEO}	I_C = 2 mA, I_B = 0	20			V
Emitter-base voltage	V_{EBO}	I_E = 10 μA, I_C = 0	5			V
Forward current transfer ratio	h_{FE}	V_{CE} = 10 V, I_C = 1 mA	70		250	
Transition frequency	f_T	V_{CB} = 10 V, I_E = -1 mA, f = 200 MHz	150	230		MHz
Reverse transfer capacitance	C_{re}	V_{CB} = 10 V, I_E = -1 mA, f = 10.7 MHz		1.3		pF

■ h_{FE} Classification

Marking	KB	KC
h_{FE}	70～160	110～250